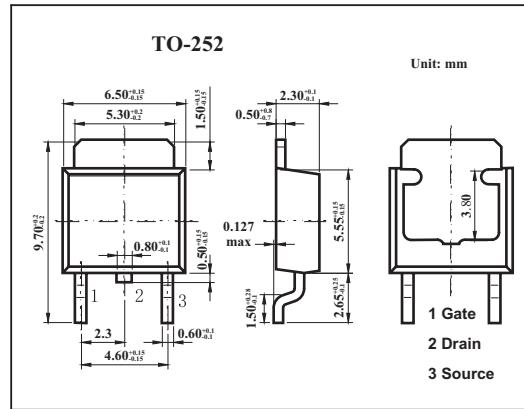
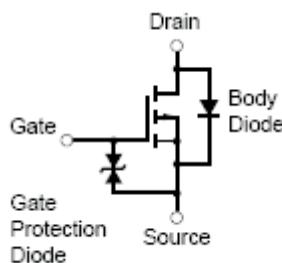


## MOS Field Effect Transistor

### 2SJ601

#### ■ Features

- Low on-resistance  
 $R_{DS(on)1} = 31 \text{ m}\Omega$  MAX. ( $V_{GS} = -10 \text{ V}$ ,  $I_D = -18 \text{ A}$ )  
 $R_{DS(on)2} = 46 \text{ m}\Omega$  MAX. ( $V_{GS} = -4.0 \text{ V}$ ,  $I_D = -18 \text{ A}$ )
- Low  $C_{iss}$ :  $C_{iss} = 3300 \text{ pF TYP.}$
- Built-in gate protection diode



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current (DC)	$I_D$	$\pm 36$	A
Drain current(pulse) *	$I_D$	$\pm 120$	A
Power dissipation	$P_D$	65	W
$T_c=25^\circ\text{C}$			
$T_A=25^\circ\text{C}$	$P_D$	1.0	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$

**2SJ601**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	$I_{DSS}$	$V_{DS}=-60V, V_{GS}=0$			-10	$\mu\text{A}$
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0$			$\pm 10$	$\mu\text{A}$
Gate to source cutoff voltage	$V_{GS(\text{off})}$	$V_{DS}=-10V, I_D=-1\text{mA}$	1.5	2.0	2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=-10V, I_D=-18\text{A}$	10	30		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-18\text{A}$		25	31	$\text{m}\Omega$
		$V_{GS}=-4.0V, I_D=-18\text{A}$		32	46	$\text{m}\Omega$
Input capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0, f=1\text{MHz}$		3300		pF
Output capacitance	$C_{oss}$			580		pF
Reverse transfer capacitance	$C_{rss}$			230		pF
Turn-on delay time	$t_{d(on)}$	$V_{GS(\text{on})}=-30V, I_D=-18\text{A}, V_{DD}=-10V, R_G=0\Omega$		11		ns
Rise time	$t_r$			12		ns
Turn-off delay time	$t_{d(off)}$			80		ns
Fall time	$t_f$			53		ns
Total Gate Charge	$Q_G$	$I_D = -36\text{A}$ $V_{DD} = -48\text{V}$ $V_{GS} = -10\text{V}$		63		nC
Gate to Source Charge	$Q_{GS}$			10		nC
Gate to Drain Charge	$Q_{GD}$			16		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = -36\text{A}, V_{GS} = 0\text{V}$		1.0		V
Reverse Recovery Time	$t_{rr}$	$I_F = -36\text{A}, V_{GS} = 0\text{V}$		52		ns
Reverse Recovery Charge	$Q_{rr}$	$dI/dt = 100\text{A}/\mu\text{s}$		108		nC